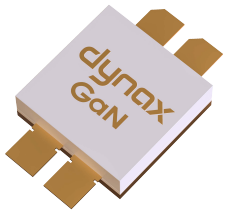
DXG1CH19A-100EF

RF Power GaN Transistor



1. Product profile

1.1 General description

DXG1CH19A-100EF is a 100 W RF GaN HEMT Transistor with first generation RF GaN technology from Dynax, which is ideal for cellular base station applications at frequencies from 1805 MHz to 2170 MHz.

Table 1. Typical performance

Freq (MHz)	P_{sat} [1] (dBm)	P_{avg} [2] (dBm)	η_D [2] (%)	G_P [2] (dB)	ACPR [2] (dBc)
2110~2170	50.0	41.7	58.0	16.8	-30.0

[1] Test condition: Pulsed CW, Pulse width = 100 µs, Duty cycle = 10 %.

[2] Typical Doherty performance in Dynax Demo with the device soldered onto the heatsink, test condition: V_{DS} = 48 V, I_{DQA} = 80 mA, V_{GSB} = - 5.2 V, Single-Carrier W-CDMA, IQ magnitude clipping, Input signal PAR = 7.5 dB @ 0.01 % probability on CCDF. ACPR measured in 3.84 MHz channel bandwidth @ ± 5 MHz offset.

1.2 Features and benefits

- High efficiency, high gain
- Internally matched for broadband performance
- Designed for Digital Pre-Distortion error correction systems
- Optimized for Doherty applications

1.3 Applications

- RF power amplifier for base stations and multi carrier applications in the 2110 MHz to 2170 MHz frequency range

1.4 Lead-free and RoHS compliant

2. Pinning information

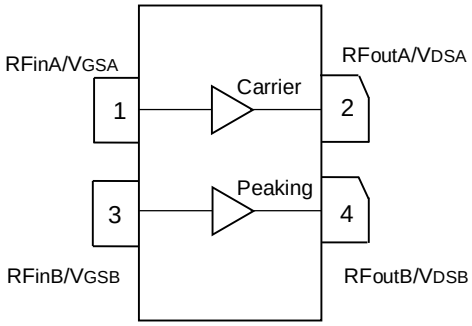


Fig 1. Pin configuration (Top view)

3. Ordering information

Table 2. Ordering information

Part number	Marking	Package type	Packaging information
DXG1CH19A-100EF	DXG1CH19A-100EF	400P2AA	Tray: Suffix = 20 units
			Tape and Reel: Suffix = 100 units; 24 mm Tape width; 13-inch Reel

4. Maximum ratings

Table 3. Maximum ratings

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	150	V
Gate-Source Voltage	V_{GS}	-10 ~ +2	V
Operating Voltage	V_{DS}	0 ~ +55	V
Maximum Forward Gate Current	I_{GMAX}	11.2	mA
Storage Temperature Range	T_{STG}	- 65 ~ +150	℃
Operating Junction Temperature	T_J	225	℃
Absolute Maximum Channel Temperature [1]	T_{MAX}	275	℃

[1] Functional operation above 225℃ has not been characterized and is not implied. Operation at T_{MAX} (275℃) reduces median time to failure by an order of magnitude; Operation beyond T_{MAX} could cause permanent damage.

5. Thermal characteristics

Table 4. Thermal characteristics

Parameter	Symbol	Value	Unit
Side A, Carrier			
Thermal Resistance at Average Power by Infrared Measurement, Active Die Surface-to-Case $T_{base\text{-}plate}$ = 85℃, P_D = 8.8 W	R_{thjc}(IR)	4.5	℃/W
Thermal Resistance at Average Power by Finite Element Analysis, Junction-to-Case $T_{base\text{-}plate}$ = 85℃, P_D = 8.8 W	R_{thjc}(FEA)	5.8	℃/W
Side B, Peaking			
Thermal Resistance at Average Power by Infrared Measurement, Active Die Surface-to-Case $T_{base\text{-}plate}$ = 85℃, P_D = 2.2 W	R_{thjc}(IR)	3.1	℃/W
Thermal Resistance at Average Power by Finite Element Analysis, Junction-to-Case $T_{base\text{-}plate}$ = 85℃, P_D = 2.2 W	R_{thjc}(FEA)	3.9	℃/W

6. ESD protection characteristics

Table 5. ESD protection characteristics

Test methodology	Class
Human Body Model (per JS-001-2012)	1A (> 250 V)
Charged Device Model (per JESD22-C101F)	C2 (> 500 V)

7. Moisture sensitivity level

Table 6. Moisture sensitivity level

Test methodology	Class
Moisture Sensitivity Level (per J-STD-020)	Level 1

8. Electrical characteristics (TA = 25℃ unless otherwise noted)

Table 7. DC characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Side A, Carrier					
Drain-Source Leakage Current (V_{GS} = -10 V, V_{DS} = 150 V)	I_{DSS}	-	-	4.8	mA
Drain-Source Breakdown Voltage (V_{GS} = -10 V, I_D = 4.8 mA)	$V_{(BR)DSS}$	150	-	-	V
Gate Threshold Voltage (V_{DS} = 48 V, I_D = 4.8 mA)	$V_{GS(th)}$	-4.0	-3.2	-1.0	V
Gate Quiescent Voltage (V_{DS} = 48 V, I_D = 80 mA)	$V_{GS(Q)}$	-	-3.0	-	V
Side B, Peaking					
Drain-Source Leakage Current (V_{GS} = -10 V, V_{DS} = 150 V)	I_{DSS}	-	-	6.4	mA
Drain-Source Breakdown Voltage (V_{GS} = -10 V, I_D = 6.4 mA)	$V_{(BR)DSS}$	150	-	-	V
Gate Threshold Voltage (V_{DS} = 48 V, I_D = 6.4 mA)	$V_{GS(th)}$	-4.0	-3.2	-1.0	V
Gate Quiescent Voltage (V_{DS} = 48 V, I_D = 120 mA)	$V_{GS(Q)}$	-	-3.0	-	V

Table 8. RF characteristics (Typical Doherty performance – 2170 MHz) [1]

Parameter	Symbol	Min.	Typ.	Max.	Unit
Peak Output Power [2]	P_{sat}	49.3	50.3	-	dBm
Drain Efficiency [3]	η_D	49.9	56.9	-	%
Power Gain [3]	G_P	15.2	16.8	18.4	dB

[1] Typical Doherty performance in Dynax DXG1CH19A-100EF production test fixture, test condition: V_{DS} = 48 V, I_{DQA} = 80 mA, V_{GSB} = -2.3 V + V_{GSQ} @120 mA.

[2] Test condition: Pulsed CW, Pulse width = 100 µs, Duty cycle = 10 %.

[3] Test condition: P_{out} = 41.7 dBm Avg., Single-Carrier W-CDMA, IQ magnitude clipping, Input signal PAR = 7.5 dB @ 0.01 % probability on CCDF.

Table 9. Load mismatch

Parameter	Result
VSWR 10:1 at V_{DS} = 48 V, 100 W Pulsed CW output power, Pulse width = 100 µs, Duty cycle = 10%.	No device damage

9. Test information

9.1 Typical application circuit

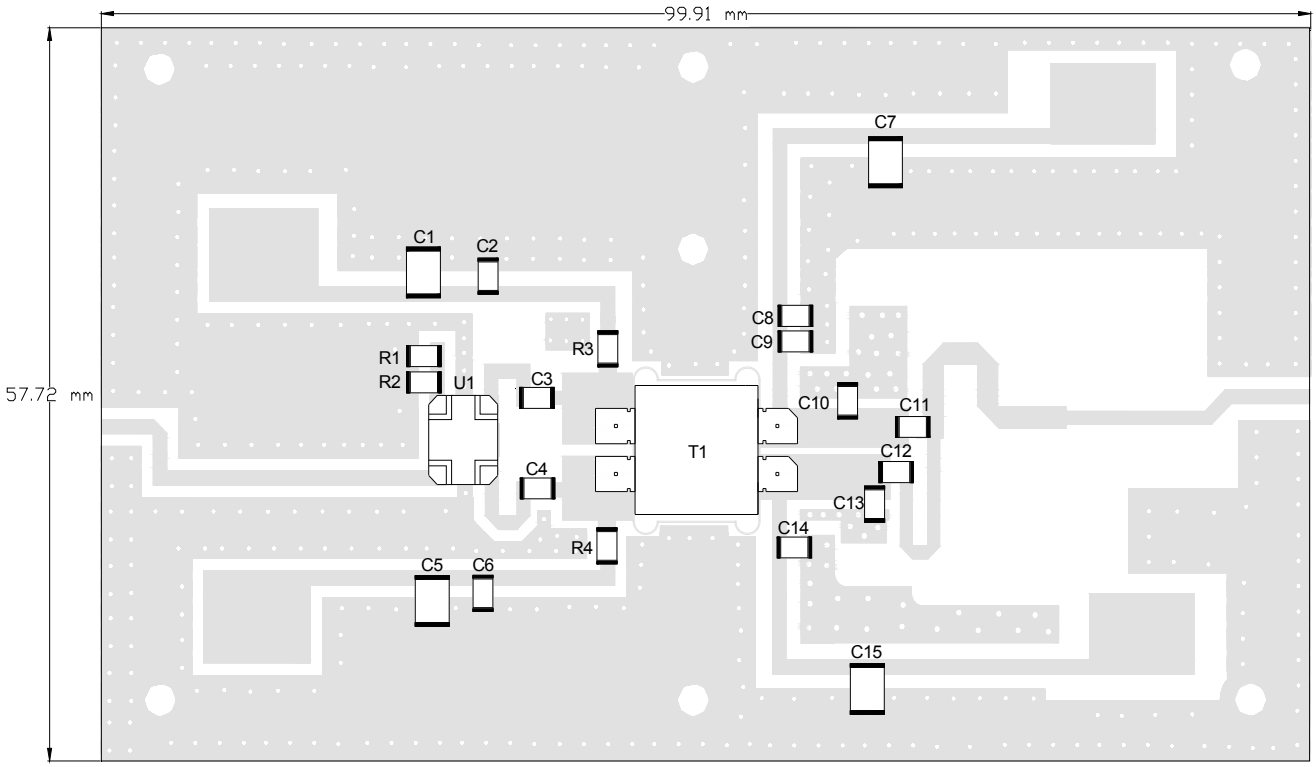


Fig 2. Component layout

Table 10. List of components

S/N	Type	Designator	Description	Value	Vendor
1	Cap	C2,C3,C4,C6,C12,C14	ATC600F100JT250XT	10 pF	ATC
2	Cap	C1,C5,C7,C15	GRM31CZ72A106KE	10 uF	Murata
3	Cap	C8,C9,C11	ATC600F150JT250XT	15 pF	ATC
4	Cap	C10	ATC600F1R5BT250T	1.5 pF	ATC
5	Cap	C13	ATC600F0R8JT250XT	0.8 pF	ATC
6	Res	R3,R4	RC0805FR_0710RL	10 Ω	Yageo
7	Res	R1,R2	RC0805FR_07100RL	100 Ω	Yageo
8	HyBrid coupler	U1	CMX21Q03	3 dB	RN2
9	Transistor	T1	DXG1CH19A-100EF	/	Dynax

9.2 Graphic data

9.2.1 Pulsed CW

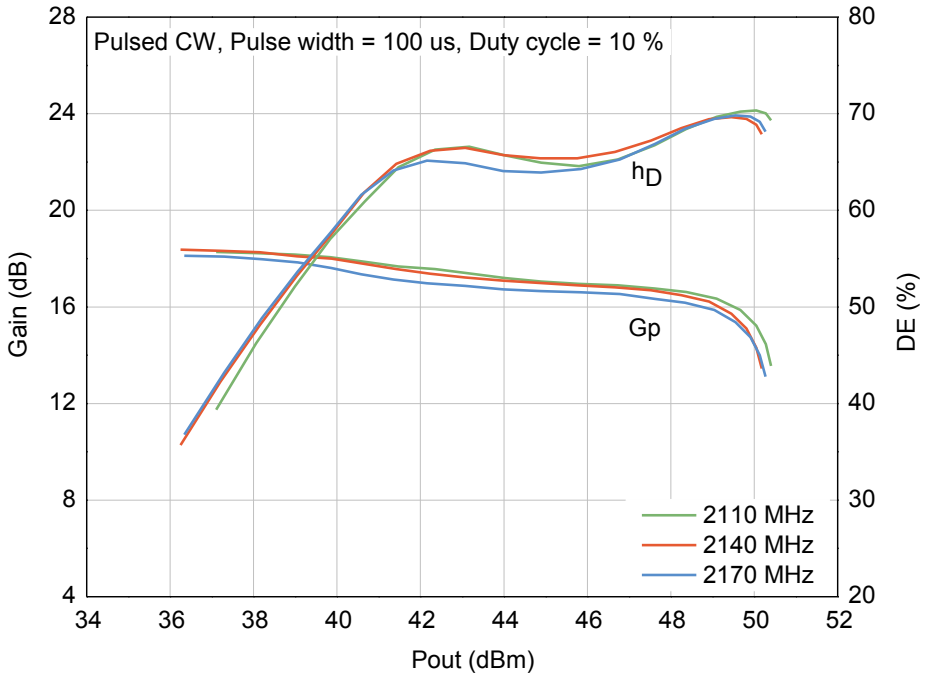


Fig 3. Power gain, Drain efficiency vs. Pulse output power

10. Impedance information

Table 11. Typical impedance of carrier [1]

Maximum Output Power						
Freq (MHz)	Z_S (Ω)	Z_L (Ω)	G_P (dB)	P_{sat} (dBm)	P_{sat} (W)	η_D (%)
1805	5.7 - j17.1	11.7 + j0.3	22.4	47.2	52	74.6
1880	5.0 - j19.7	12.5 - j0.7	22.3	47.2	52	74.3
2110	15.4 - j34.1	8.9 - j0.8	21.9	46.8	47	75.3
2170	21.5 - j38.5	7.6 - j1.1	21.5	46.8	47	74.3
Maximum Drain Efficiency						
Freq (MHz)	Z_S (Ω)	Z_L (Ω)	G_P (dB)	P_{sat} (dBm)	P_{sat} (W)	η_D (%)
1805	5.7 - j17.1	8.8 + j12.0	23.2	44.5	28	84.0
1880	5.0 - j19.7	7.8 + j10.0	23.4	44.5	28	84.5
2110	15.4 - j34.1	7.4 + j7.0	22.7	44.4	27	84.9
2170	21.5 - j38.5	6.5 + j7.1	22.1	44.3	27	85.1

Table 12. Typical impedance of peaking [2]

Maximum Output Power						
Freq (MHz)	Z_S (Ω)	Z_L (Ω)	G_P (dB)	P_{sat} (dBm)	P_{sat} (W)	η_D (%)
1805	6.8 - j31.5	8.4 + j0.9	23.0	48.3	67	73.2
1880	12.2 - j36.3	9.2 + j0.0	23.1	48.3	67	73.5
2110	81.1 - j29.0	6.6 - j0.8	22.2	48.1	64	73.8
2170	46.1 + j42.2	5.2 - j0.5	21.7	47.9	62	73.7
Maximum Drain Efficiency						
Freq (MHz)	Z_S (Ω)	Z_L (Ω)	G_P (dB)	P_{sat} (dBm)	P_{sat} (W)	η_D (%)
1805	6.8 - j31.5	6.4 + j9.2	24.7	45.5	35	83.1
1880	12.2 - j36.3	5.5 + j6.6	24.7	45.5	35	82.2
2110	81.1 - j29.0	4.6 + j5.7	23.8	45.3	33	84.1
2170	46.1 + j42.2	4.0 + j5.8	23.3	45.1	32	84.5

[1] V_{DS} = 48 V, I_{DQA} = 80 mA, Pulsed CW, Pulse width = 100 µs, Duty cycle = 10 %.

[2] V_{DS} = 48 V, I_{DQB} = 120 mA, Pulsed CW, Pulse width = 100 µs, Duty cycle = 10 %.

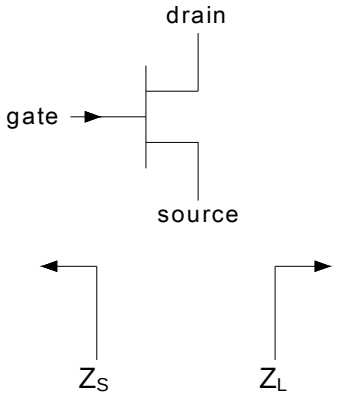


Fig 4. Definition of Transistor Impedance

11. Median lifetime

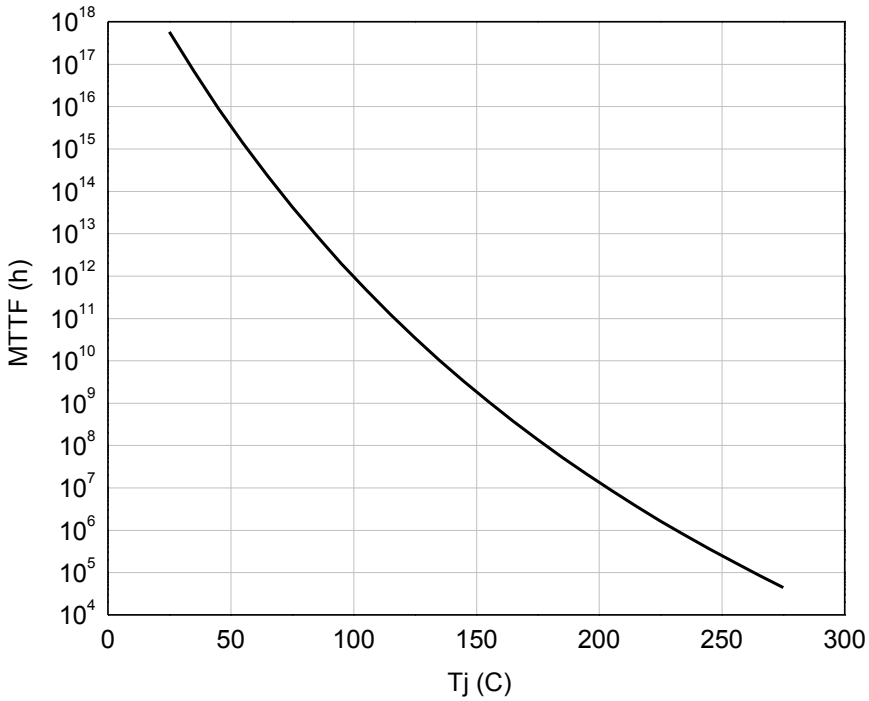
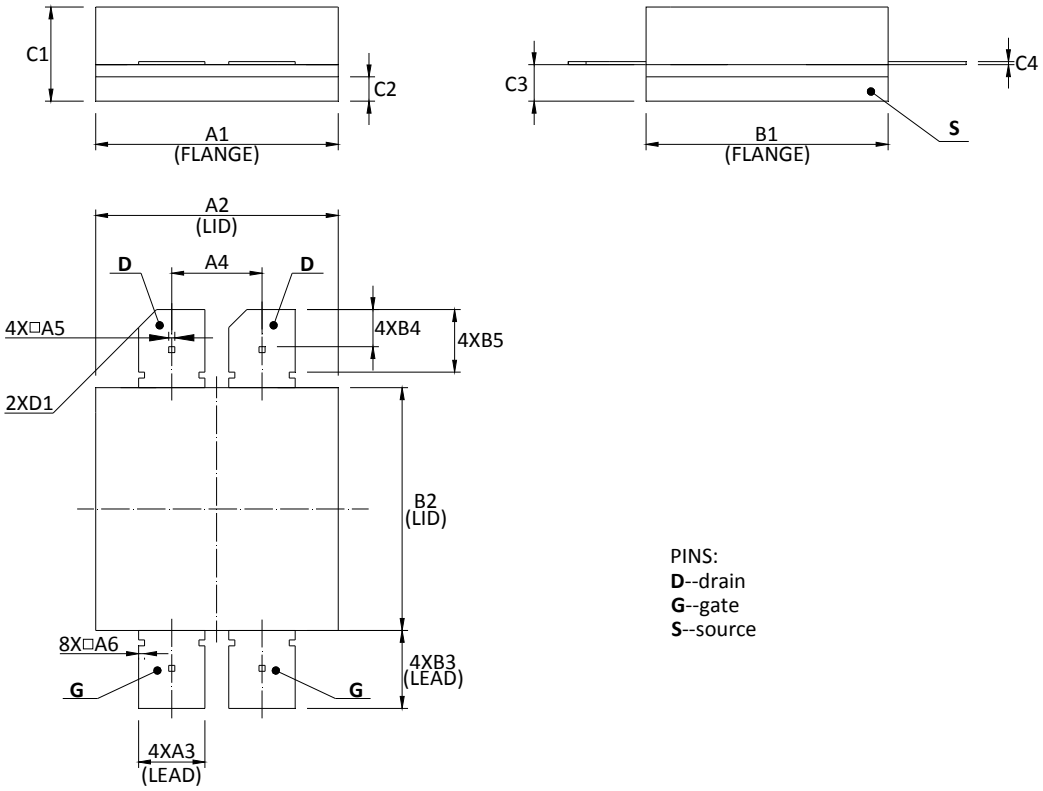


Fig 5. Median lifetime vs. channel temperature

12. Package outline



DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX
A1	0.395	0.405	10.033	10.287
A2	0.393	0.405	9.983	10.287
A3	0.105	0.115	2.667	2.921
A4	0.144	0.154	3.657	3.912
A5	0.005	0.015	0.125	0.375
A6	0.005	0.015	0.125	0.375
B1	0.395	0.405	10.033	10.287
B2	0.393	0.405	9.983	10.287
B3	0.108	0.148	2.765	3.765
B4	0.041	0.081	1.050	2.050
B5	0.083	0.123	2.120	3.120
C1	0.147	0.167	3.733	4.242
C2	0.035	0.045	0.889	1.143
C3	0.057	0.067	1.447	1.702
C4	0.003	0.006	0.076	0.153
D1	0.03 45° REF		0.75 45° REF	

Fig 6. Package outline —— 400P2AA

13. Abbreviations

Table 13. Abbreviations

Acronym	Description
CW	Continuous Waveform
ESD	Electro-Static Discharge
GaN	Gallium Nitride
HEMT	High Electron Mobility Transistor
MTTF	Median Time To Failure
VSWR	Voltage Standing Wave Ratio

14. Legal information

14.1 Datasheet status

Document status	Product status	Definition
Objective [short] datasheet	Engineering sample	This document contains data from the objective specification for product development.
Preliminary [short] datasheet	Engineering sample	This document contains data from the preliminary specification.
Production [short] datasheet	Mass product	This document contains the product specification.

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